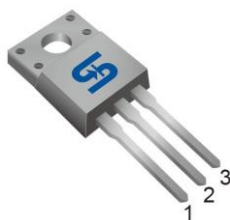
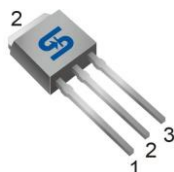


TSM60N900

600V, 4.5A, 0.9Ω
N-Channel Power MOSFET

ITO-220

**TO-251
(IPAK)**

Pin Definition:

1. Gate
2. Drain
3. Source

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	600	V
$R_{DS(on)}$ (max)	0.9	Ω
Q_g	9.7	nC

**TO-252
(DPAK)**


Features

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

Application

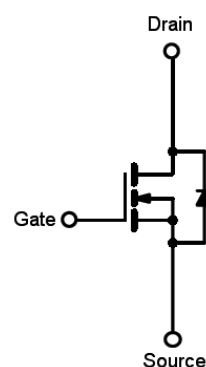
- Power Supply.
- Lighting

Ordering Information

Part No.	Package	Packing
TSM60N900CI C0G	ITO-220	50pcs / Tube
TSM60N900CH C5G	TO-251	75pcs / Tube
TSM60N900CP ROG	TO-252	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain
<900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl)
and <1000ppm antimony compounds

Block Diagram


N-Channel MOSFET

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit		Unit
		ITO-220	IPAK/DPAK	
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current ^(Note 1)	I_D	4.5		A
Pulsed Drain Current ^(Note 2)	I_{DM}	13.5		A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	20	50	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	81		mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	1.8		A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150		$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit		Unit
		ITO-220	IPAK/DPAK	
Junction to Case Thermal Resistance	$R_{\theta JC}$	6.25	2.5	°C/W
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62		°C/W

Electrical Specifications ($T_C = 25^\circ\text{C}$ unless otherwise noted)

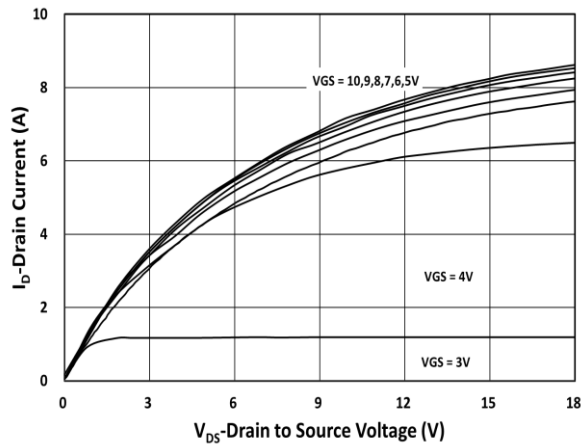
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.3A$	$R_{DS(ON)}$	--	0.72	0.9	Ω
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 380V, I_D = 2.3A,$ $V_{GS} = 10V$	Q_g	--	9.7	--	nC
Gate-Source Charge		Q_{gs}	--	2.3	--	
Gate-Drain Charge		Q_{gd}	--	3.6	--	
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	480	--	pF
Output Capacitance		C_{oss}	--	36	--	
Gate Resistance	$f=1MHz$, open drain	R_g	--	3.4	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 4.7\Omega,$ $I_D = 2.3A, V_{GS} = 10V,$	$t_{d(on)}$	--	12	--	ns
Turn-On Rise Time		t_r	--	16	--	
Turn-Off Delay Time		$t_{d(off)}$	--	22	--	
Turn-Off Fall Time		t_f	--	12	--	
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S=4.5A, V_{GS}=0V$	V_{SD}	--	--	1.4	V
Reverse Recovery Time	$V_R=200V, I_S=2.3A$ $dI_F/dt=100A/\mu s$	t_{rr}	--	179	--	ns
Reverse Recovery Charge		Q_{rr}	--	1.2	--	μC

Notes:

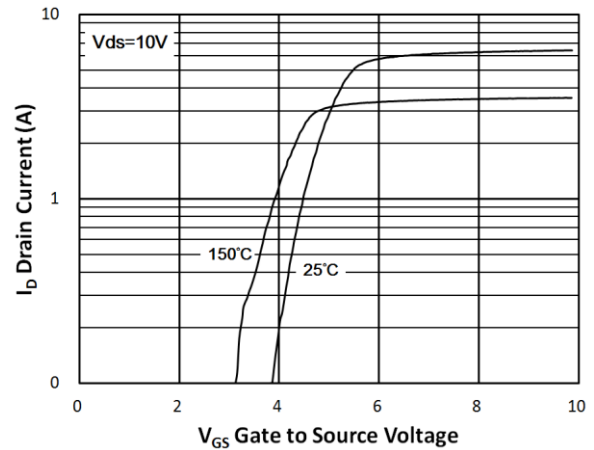
1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 50mH, I_{AS} = 1.8A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

Electrical Characteristics Curves

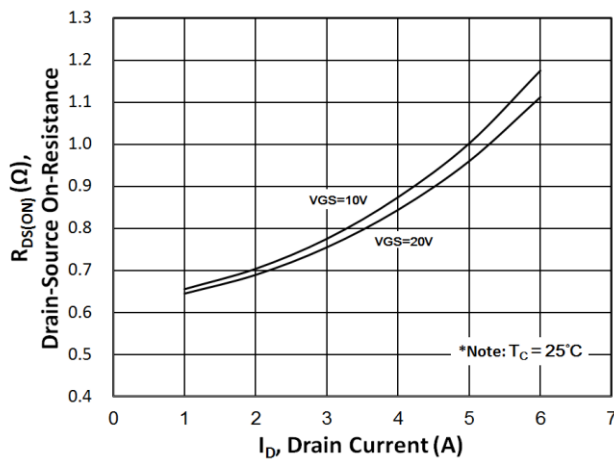
Output Characteristics



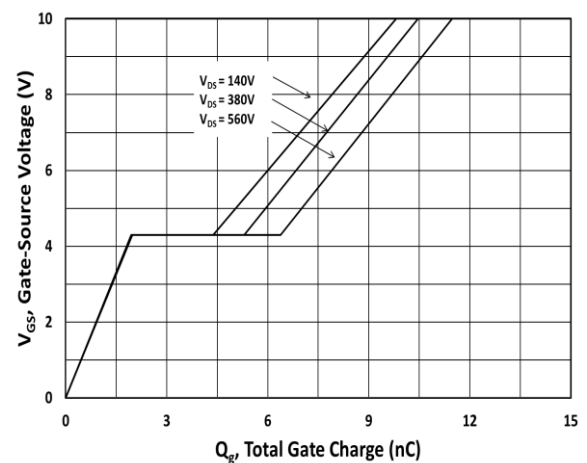
Transfer Characteristics



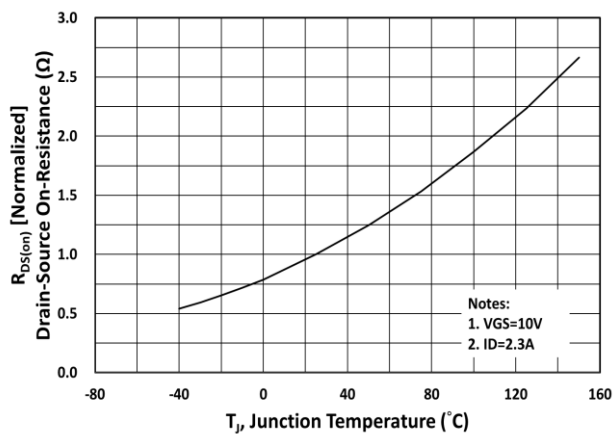
On-Resistance vs. Drain Current



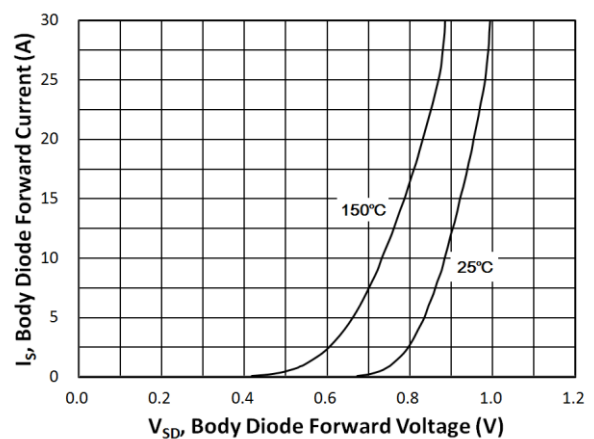
Gate Charge vs. Gate-Source Voltage



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage vs. Current

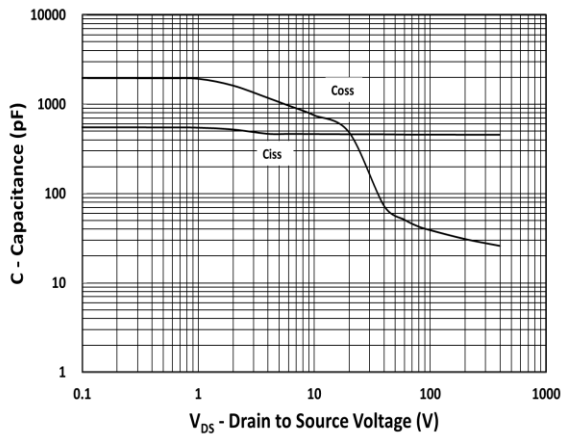


TSM60N900

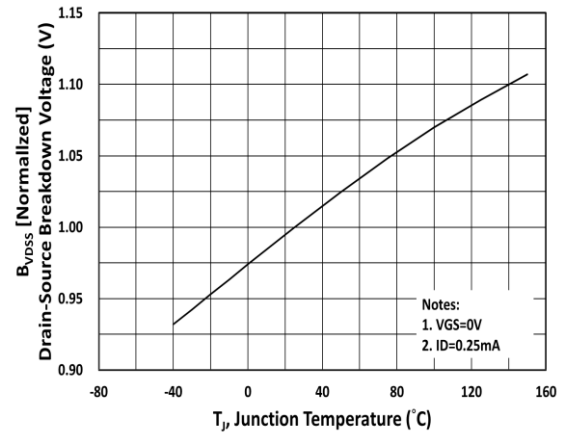
600V, 4.5A, 0.9Ω
N-Channel Power MOSFET

Electrical Characteristics Curves

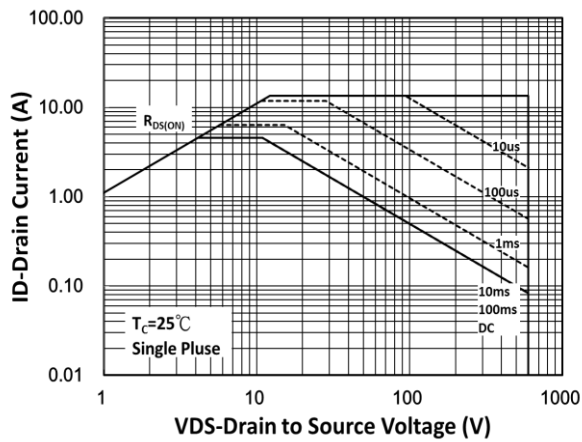
Capacitance vs. Drain-Source Voltage



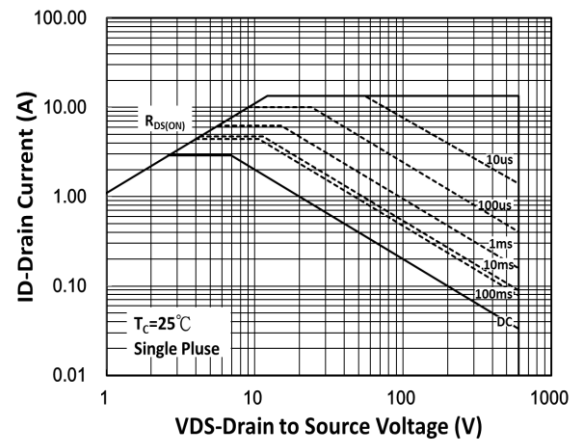
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (DPAK/IPAK)

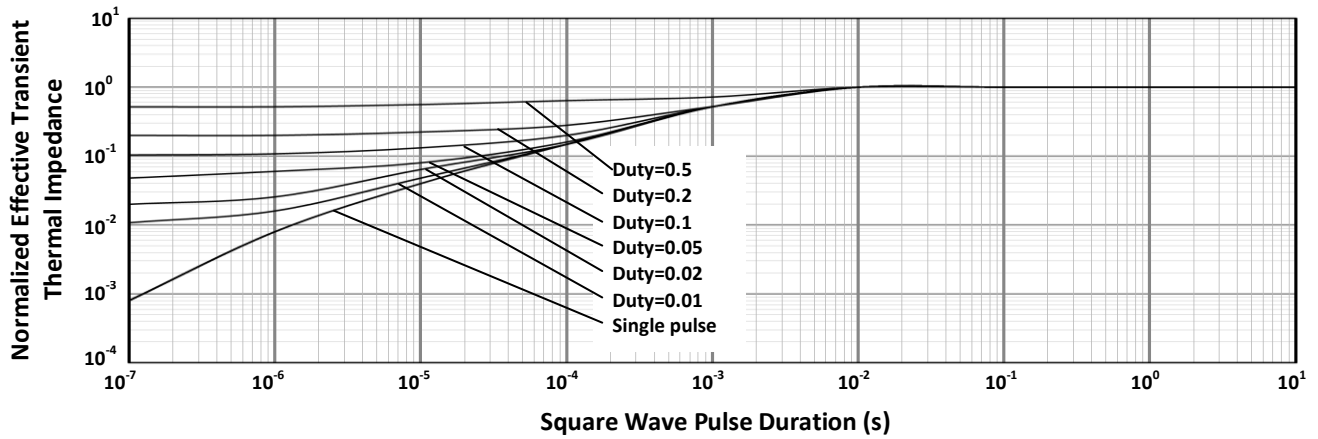


Maximum Safe Operating Area (ITO-220)

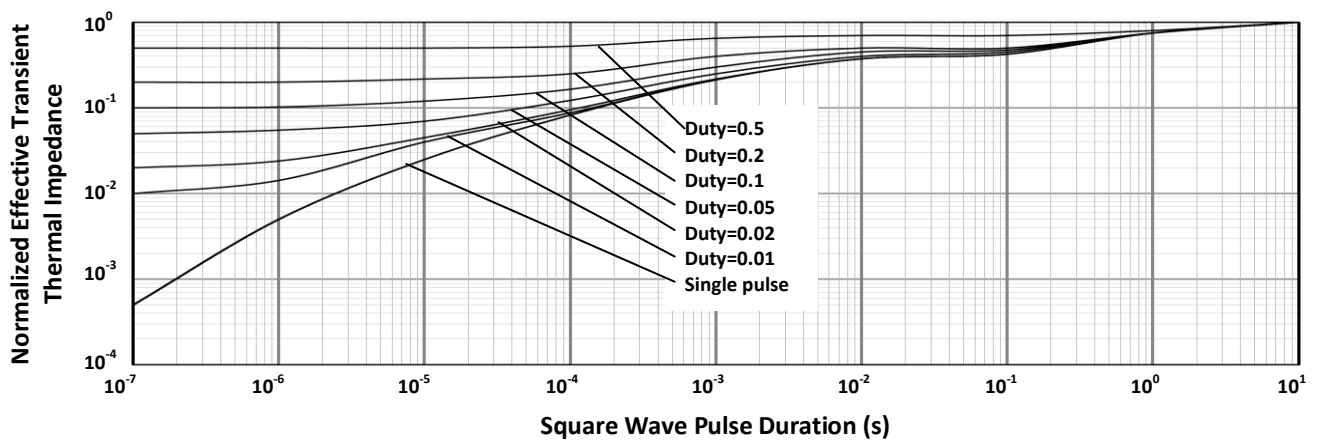


Electrical Characteristics Curves

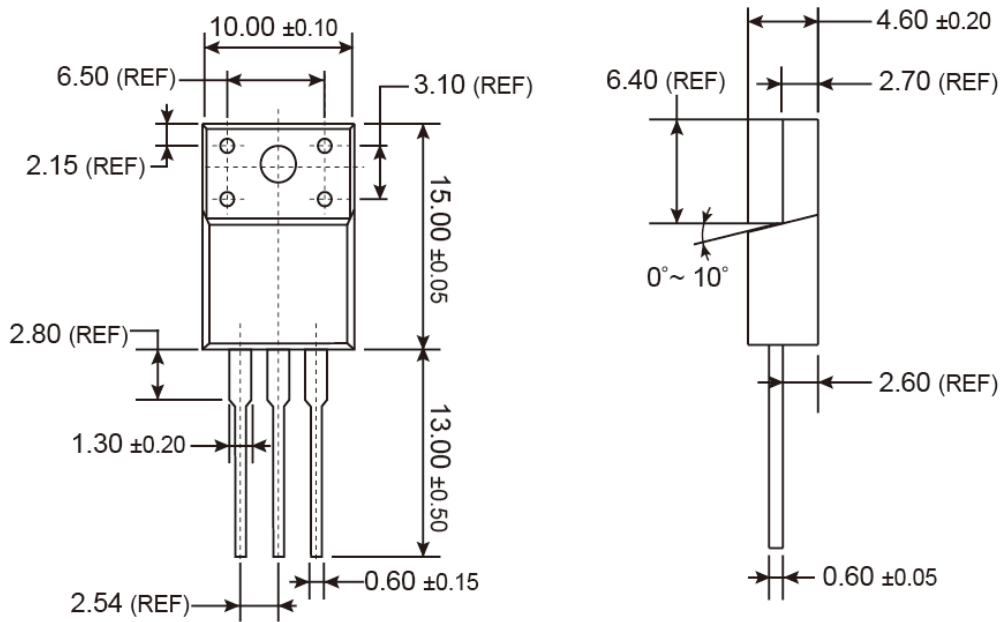
Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)



Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)

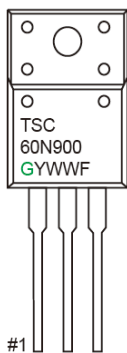


ITO-220 Mechanical Drawing



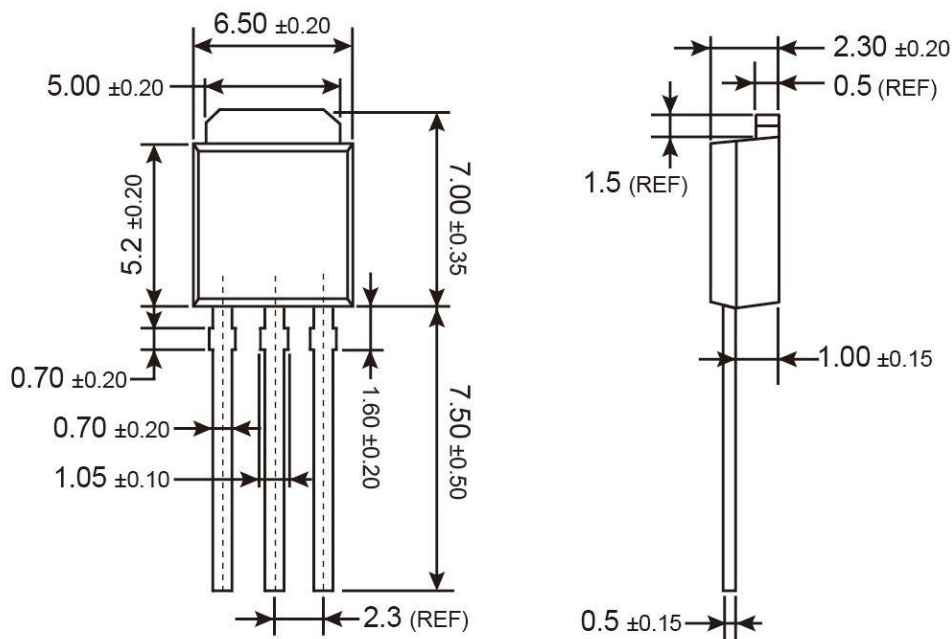
Unit: Millimeters

Marking Diagram



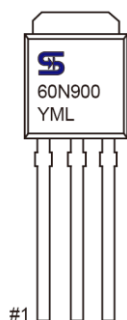
G = Halogen Free
Y = Year Code
WW = Week Code (01~52)
F = Factory Code

TO-251 (IPAK) Mechanical Drawing



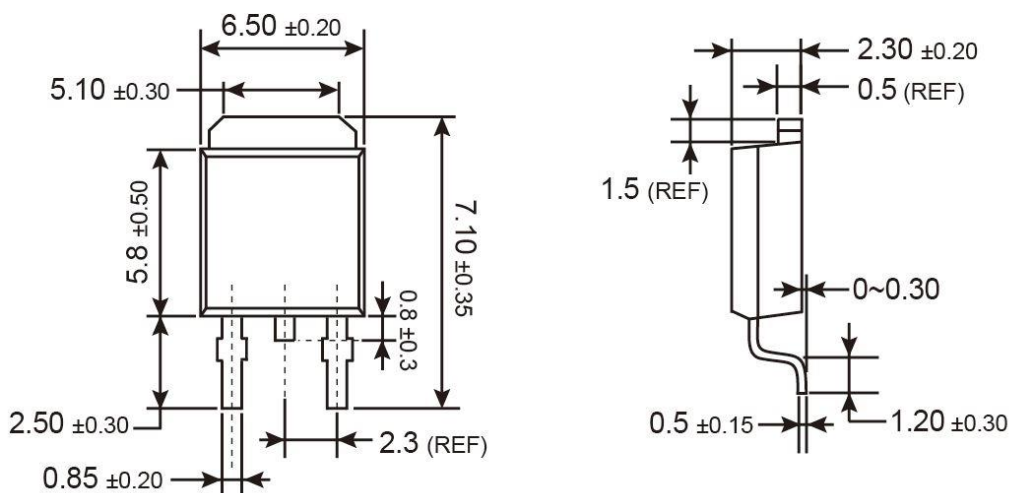
Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apr, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L** = Lot Code

TO-252 (DPAK) Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L** = Lot Code

TSM60N900

600V, 4.5A, 0.9Ω
N-Channel Power MOSFET

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